



T2035H-8E 20A TRIAC

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				80	
I_H	$I_T=500mA$		MAX.	35	mA

dV/dt $V_D=540V$ Gate Opem $A_{V(G)2(T)}T_J$ 12 244.22 132.6 519.24 T_m 1(=)4 (5) T_J 0.004 T_c

FIG.1: Maximum power dissipation versus RMS on-state current

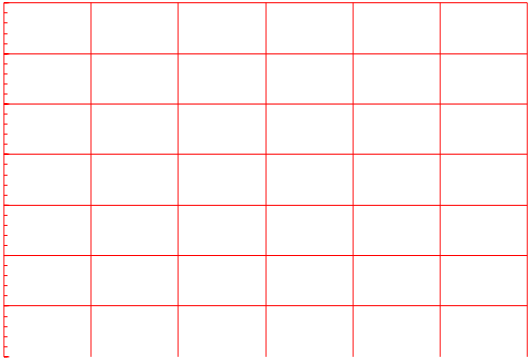


FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

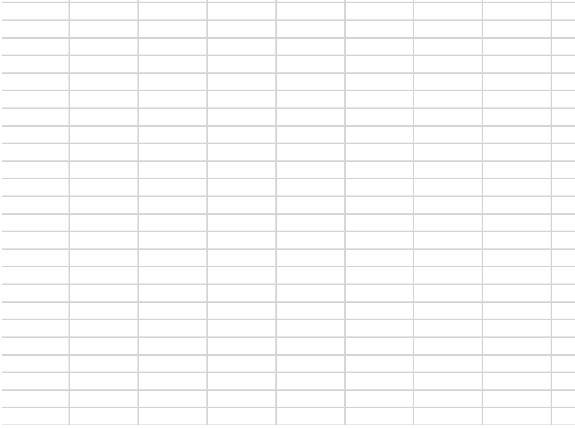
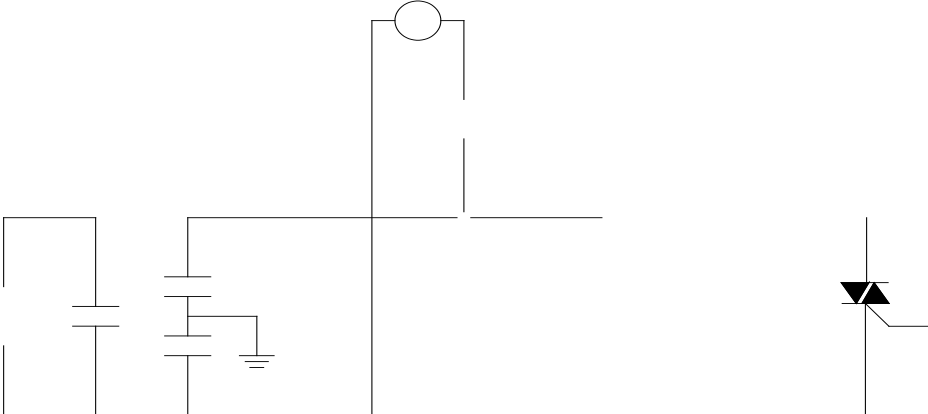


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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